

● 硅 NPN 外延平面管

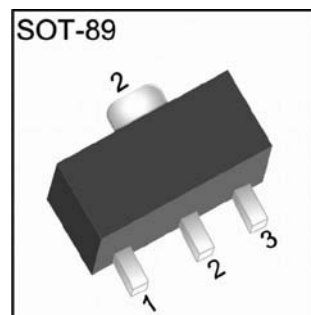
● 用途:

高频放大/振荡/混频

● 特点:

高传输频率 f_T ;

低输出电容 C_{ob} 、 C_{rb} ;



1:B 2:C 3:E

Marking Symbol: RF 09

● 极限参数($T_a=25^\circ\text{C}$)

参数	符号	单位	规范值
耗散功率	P_{tot}	W	1.0
集电极电流	I_c	mA	100
结温	$T(j)$	$^\circ\text{C}$	125
存贮温度	T_{stg}	$^\circ\text{C}$	-55~+125
集电极-基极电压	V_{CBO}	V	20
集电极-发射极电压	V_{CEO}	V	12
发射极-基极电压	V_{EBO}	V	3

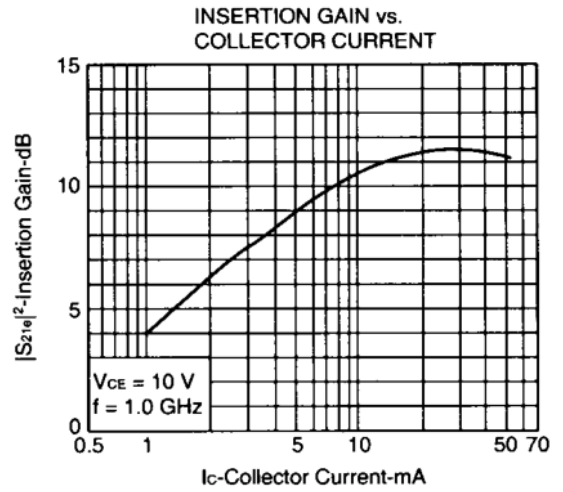
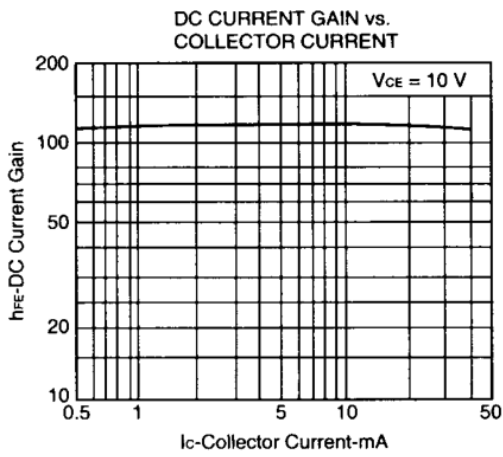
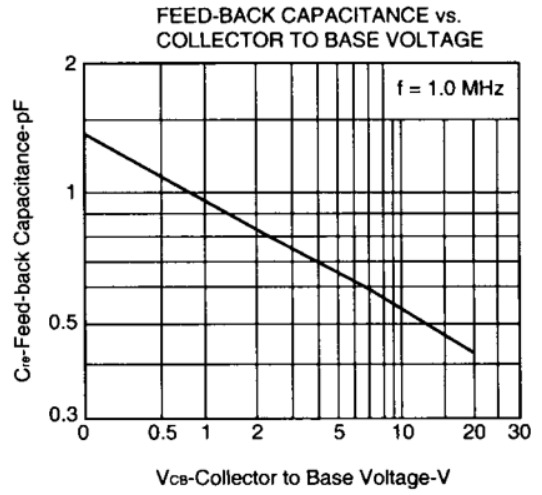
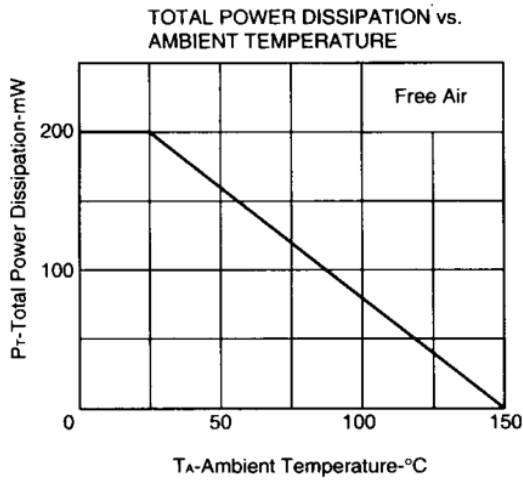
● 电参数($T_a=25^\circ\text{C}$)

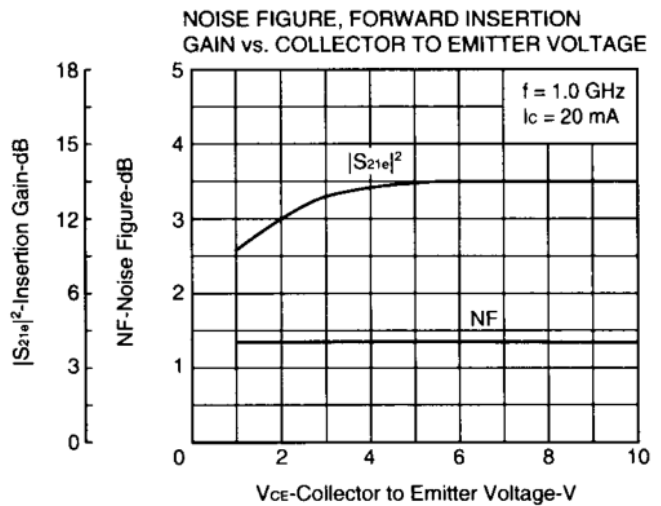
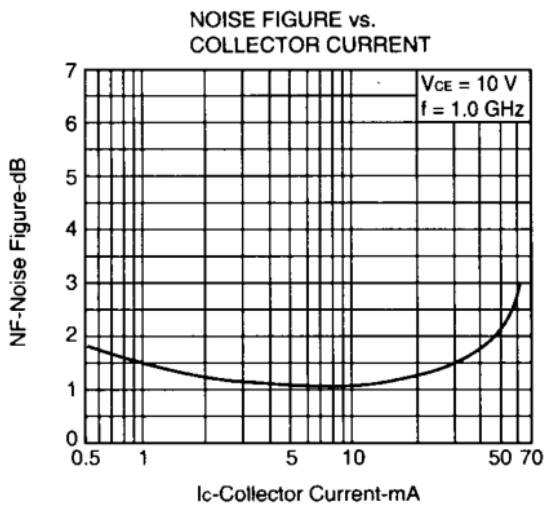
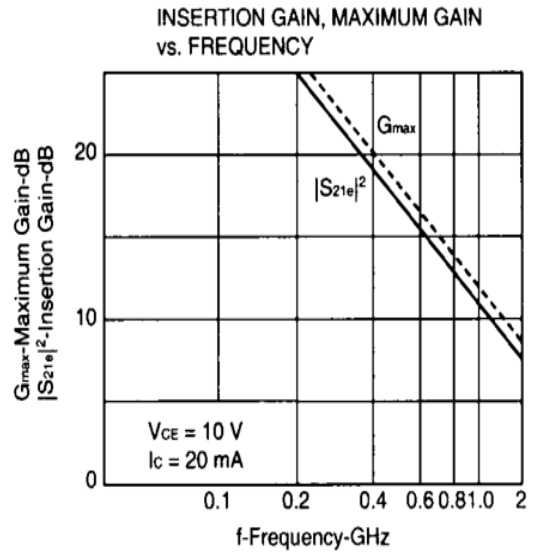
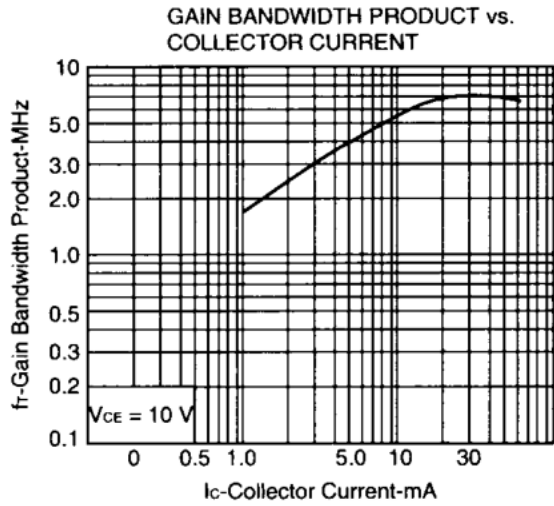
参数符号	测试条件	最小值	最大值	单位
I_{CBO}	$V_{CB}=10\text{V}$ $I_E=0$		1.0	μA
I_{CEO}	$V_{CE}=12\text{V}$ $I_B=0$		1.0	μA
I_{EBO}	$V_{EB}=1\text{V}$ $I_C=0$		90	nA
H_{FE}	$V_{CE}=10\text{V}$ $I_C=20\text{mA}$	80	250	
f_T	$V_{CE}=3\text{V}$ $I_C=20\text{mA}$	TYP: 7.0		GHz
C_{re}	$V_{CB}=3\text{V}$ $I_E=0$ $f=1\text{MHz}$	TYP: 0.75		pF
$ S_{21} _2$	$V_{CE}=3\text{V}$ $I_C=10\text{mA}$ $f=1.0\text{GHz}$	TYP: 10		dB
NF	$V_{CE}=3\text{V}$ $I_C=10\text{mA}$ $f=1.0\text{GHz}$	TYP: 1.1		dB

● H_{FE} 分档

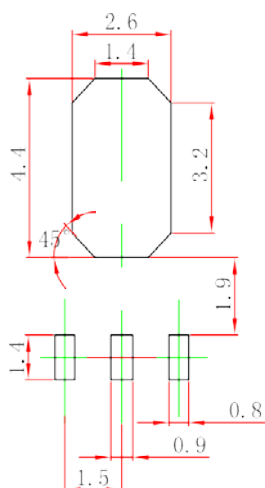
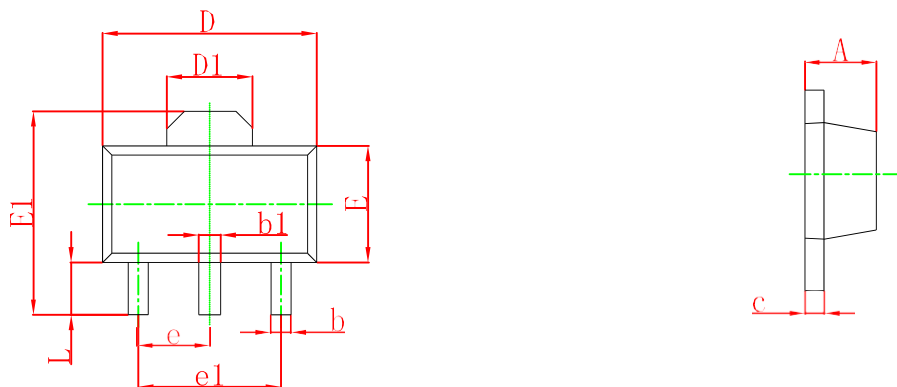
Rank	A	B	C
H_{FE}	80~120	120~180	180~250

● 典型特征曲线 (TA=25°C)





● DIMENTION SOT-89 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047